

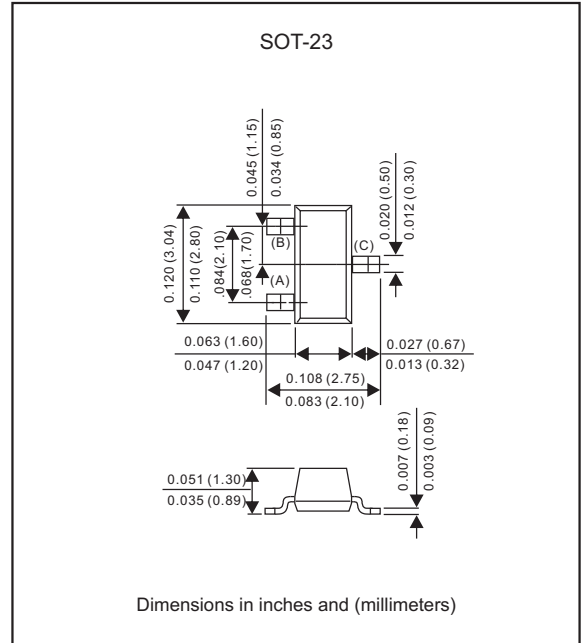
Features

- Epitaxial plana chip construction
- Ideal for medium power application and switching
- Capable of 225mW power dissipation.
- Lead-free parts for green partner, exceeds environmental standards of MIL-STD-19500 /228
- Compliant to Halogen-free

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-23
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any

Package outline



Maximum ratings (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter -Base Voltage	V_{EBO}	-5	V
Collector Current-Continuous	I_C	-600	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55-+150	$^{\circ}\text{C}$
Thermal resistance From junction to ambient	$R_{\theta JA}$	417	$^{\circ}\text{C/W}$

Characteristics (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameters	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{V}, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEX}	$V_{CE} = -35\text{V}, V_{EB} = -0.4\text{V}$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE1}	$V_{CE} = -1\text{V}, I_C = -0.1\text{mA}$	30			
	h_{FE2}	$V_{CE} = -1\text{V}, I_C = -1\text{mA}$	60			
	h_{FE3}	$V_{CE} = -1\text{V}, I_C = -10\text{mA}$	100			
	h_{FE4}	$V_{CE} = -2\text{V}, I_C = -150\text{mA}$	100		300	
	h_{FE5}	$V_{CE} = -2\text{V}, I_C = -500\text{mA}$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -150\text{mA}, I_B = -15\text{mA}$			-0.4	V
		$I_C = -500\text{mA}, I_B = -50\text{mA}$			-0.75	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -150\text{mA}, I_B = -15\text{mA}$			-0.95	V
		$I_C = -500\text{mA}, I_B = -50\text{mA}$			-1.3	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -20\text{mA}, f = 100\text{MHz}$	200			MHz
Delay time	t_d	$V_{CC} = -30\text{V}, V_{BE(off)} = -0.5\text{V}, I_C = -150\text{mA}, I_{B1} = -15\text{mA}$			15	ns
Rise time	t_r				20	ns
Storage time	t_s	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, I_{B1} = I_{B2} = -15\text{mA}$			225	ns
Fall time	t_f				60	ns

Switching time equivalent test circuits

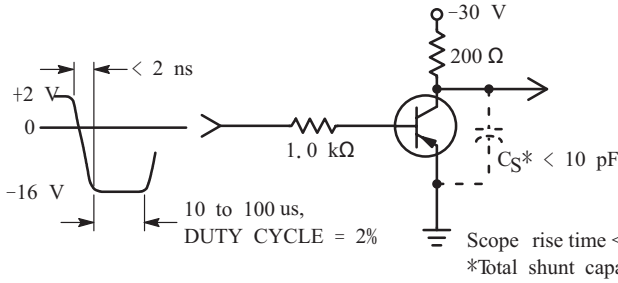


Figure 1. Turn-On Time

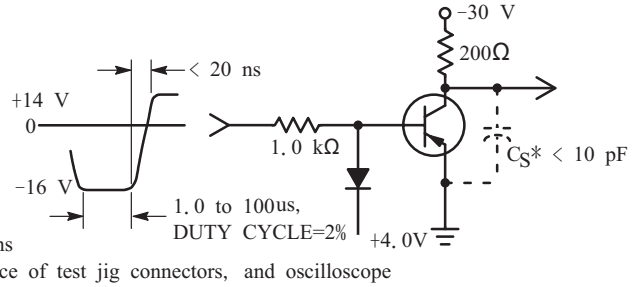


Figure 2. Turn-Off Time

TRANSIENT CHARACTERISTICS

— 25°C — 125°C

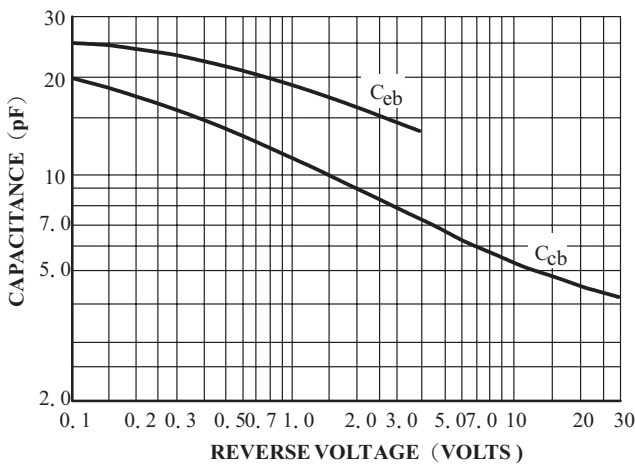


Figure 3. Capacitances

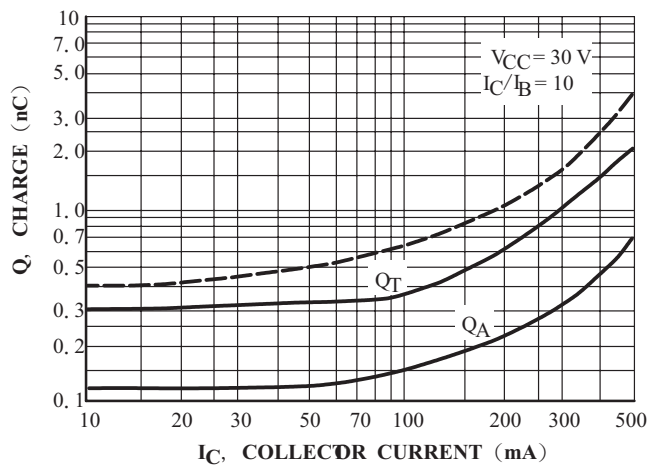


Figure 4. Charge Data

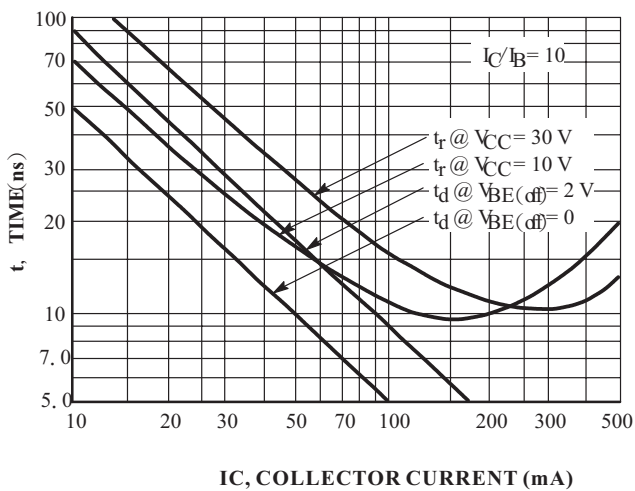


Figure 5. Turn-On Time

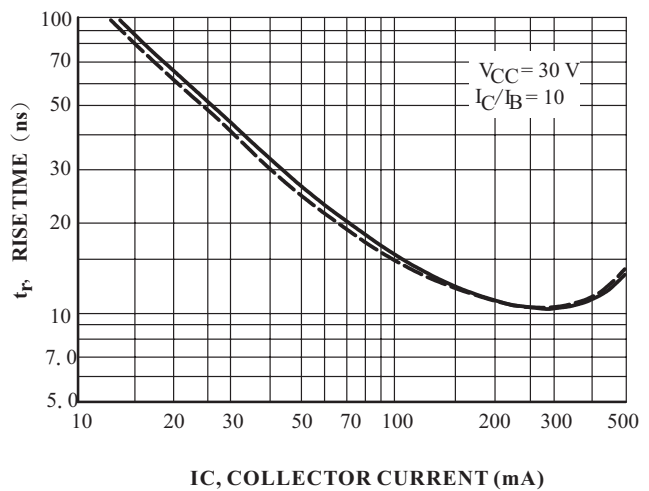


Figure 6. Rise Time

Rating and characteristic curves

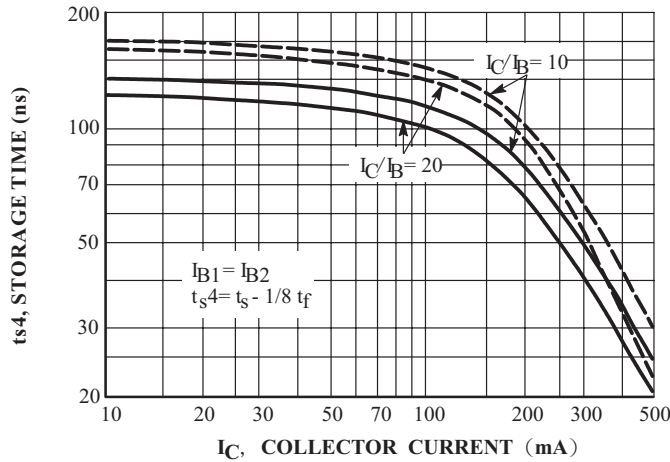


Figure 7. Storage Time

h P PARAMETERS

VCE = ±10 Vdc, f = 1.0 kHz, TA = 25°C

This group of graphs illustrates the relationship between hfe and other h parameters for this series of transistors. To

obtain these curves, a high±gain and a low±gain unit were selected from the FMBT4403 lines, and the same units were used to develop the correspondingly±numbered curves on each graph.

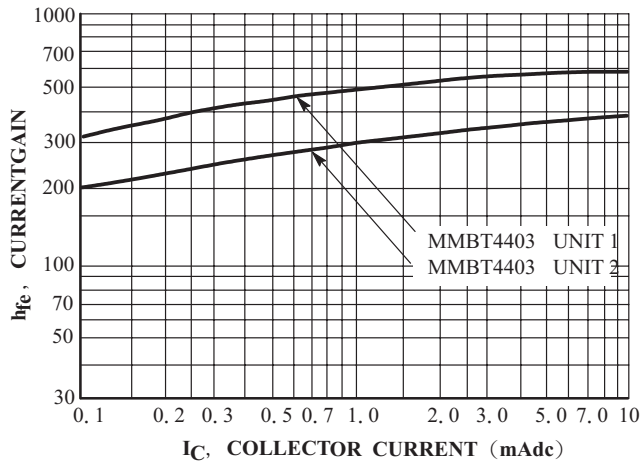


Figure 8. Current Gain

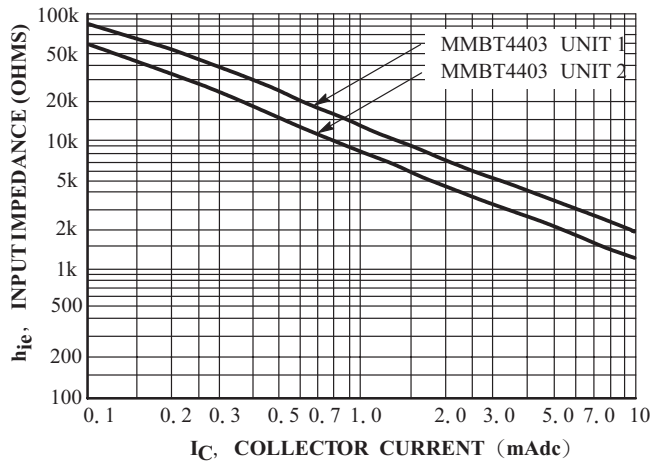


Figure 9. Input Impedance

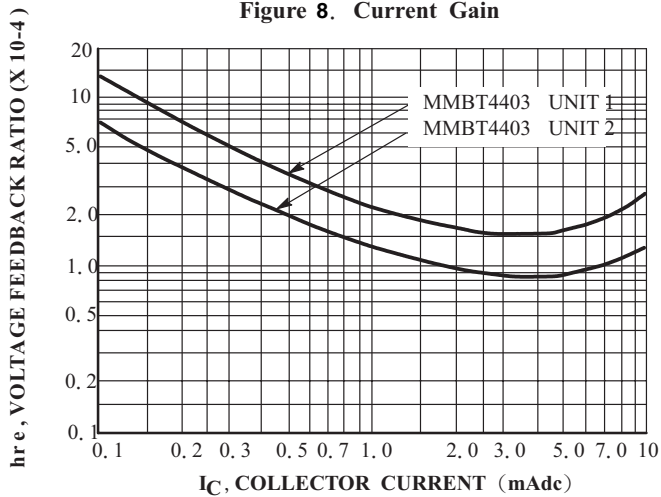


Figure 10. Voltage Feedback Ratio

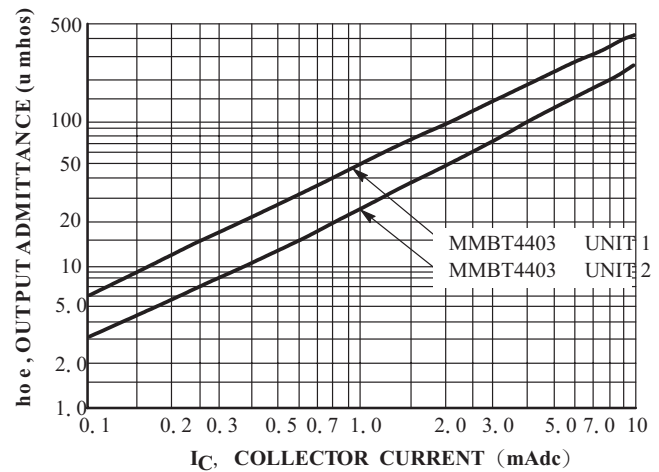


Figure 11. Output Admittance

Rating and characteristic curves

STATIC CHARACTERISTICS

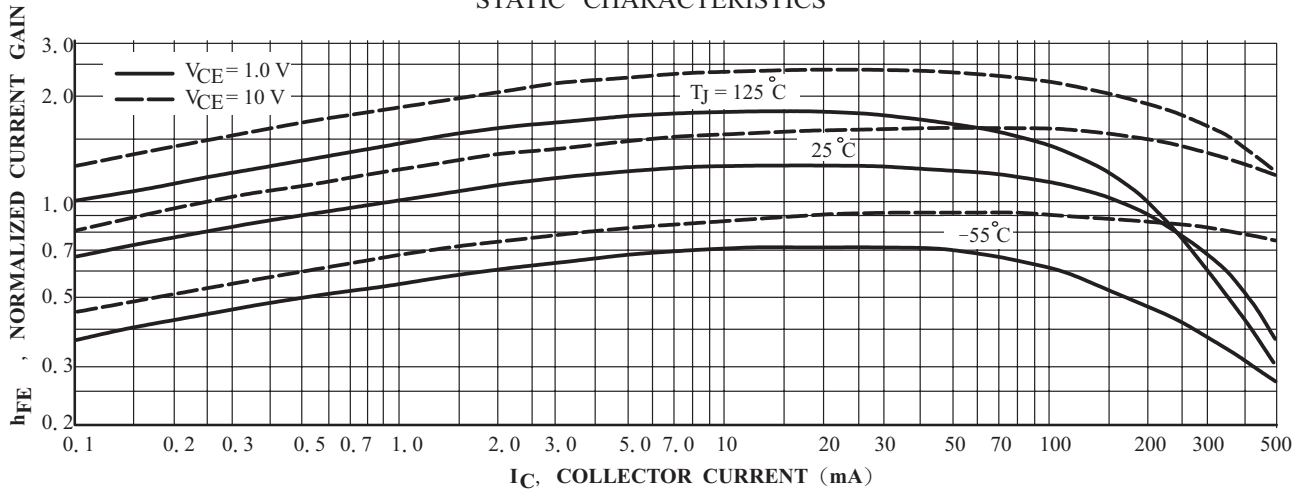


Figure 12. DC Current Gain

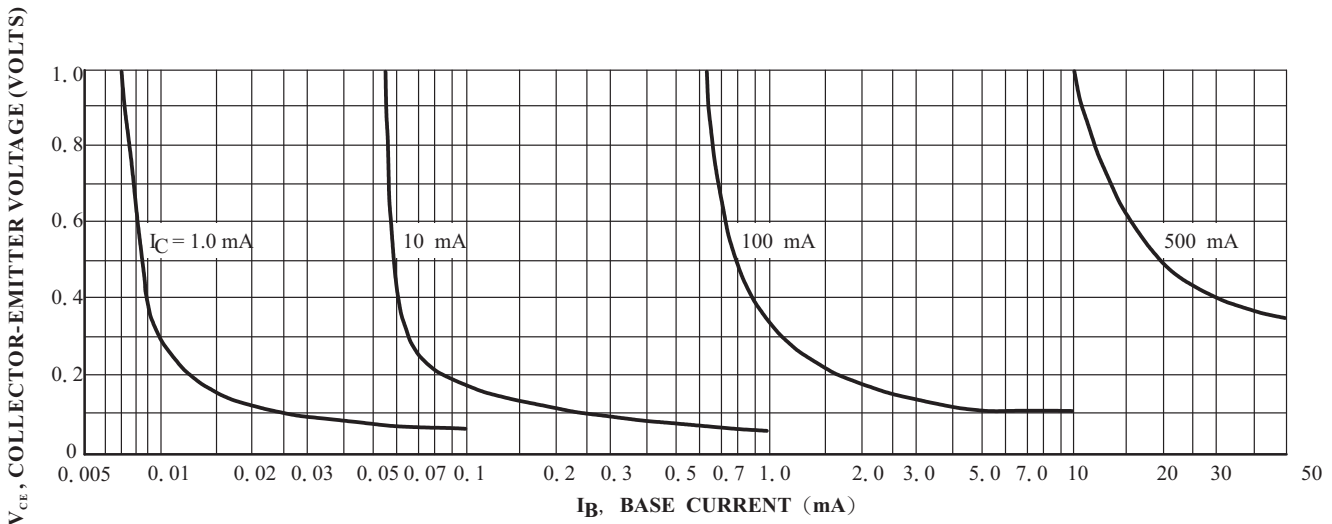


Figure 13. Collector Saturation Region

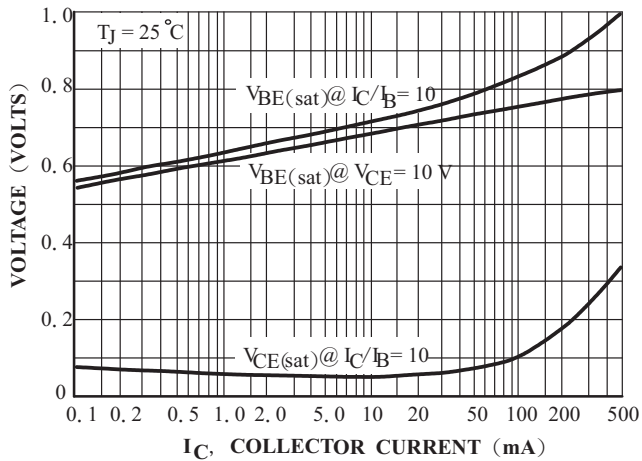


Figure 14. "On" Voltages

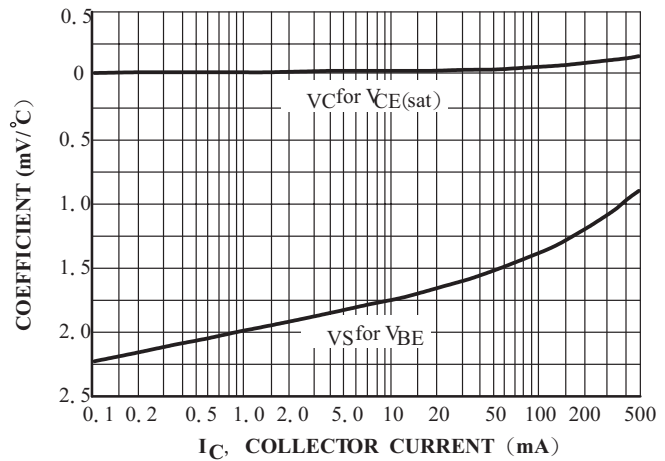
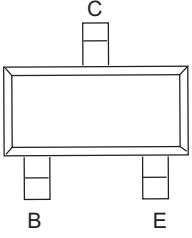
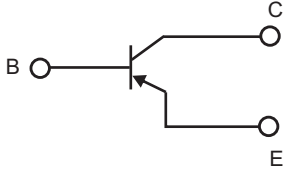


Figure 15. Temperature Coefficients

Pinning information

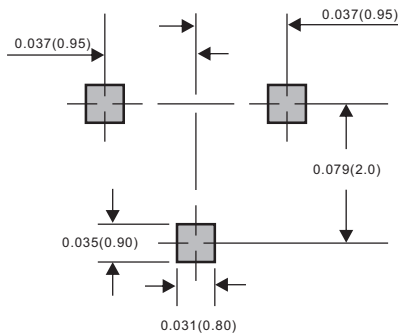
Pin	Simplified outline	Symbol
PinB Base PinC Collector PinE Emitter		

Marking

Type number	Marking code
MMBT4403	2T

Suggested solder pad layout

SOT-23



Dimensions in inches and (millimeters)